REMARKS

In the reply filed on October 1, 2004, Applicants included the following paragraph on page 14 of the Response:

New claim 68 recites a "discontinuous lateral conduction layer", and claim 88 recites "... a lateral conduction layer deposited on said substrate....and forming a contact region...". The Examiner suggests that the substrate (203) of JP '397 can be coated with a metal (paragraph 0066), which would purportedly read on the "lateral conduction layer" of original claim 44. However, there is absolutely nothing in such paragraph that suggests that such coating would (i) perform any electrical function, or (ii) form a contact region for, or even contact a region of, the bypass diode. In fact, to the contrary, as set forth in paragraph 0067, the application of a conductive coating in the JP '397 device is <u>not</u> for electrical connection of components, but for improving reflectivity, and fabrication-related reasons. See the translation of paragraphs 0066 and 0067 attached hereto. With respect to claim 68, the layers of JP '397 are not "discontinuous."

However, Applicants neglected to include the translation of paragraphs 0066 and 0067 to which we referred. Applicants hereby submit the translation of paragraphs 0066 and 0067 of JP '397.

A favorable consideration of the present amendment together with the original application is respectfully requested.

Respectfully submitted,

Dated: November 30, 2004

By:

Thomas V. DelRosario, Reg. No. 46,658

WHITE & CASE LLP

1155 Avenue of the Americas

New York, NY 10036

(650) 213-0345

Partial Translation of JP 9-64397

[0066] (Conducting substrate) The conducting substrate used in the present invention is preferably a substrate having small deformation and strain at the temperature required for forming the semiconductor membrane, and having desirable strength and good conductivity. Specific examples of the conducting substrate include plate of metal such as stainless steel, aluminum and alloys thereof, iron and alloys thereof, copper and other alloys, and plate of heat resistant resin such as polyimide, polyamide, poly(ethylene terephthalate), and epoxy, and a glass plate, to which conductivity has been provided by applying an elementary metal or allow or transparent conducting oxide onto the surface of the plate by using evaporation, sputtering, or plating.

[0067] In this connection, a layer of different metal may be formed on the surface of the conducting substrate on which the semiconductor layer is to be formed, for the purpose of such as improving the reflectivity against a light of a long wavelength which arrives at the substrate, preventing the substrate material and the semiconductor layer from mutual diffusion therebetween, improving the contact between the substrate and the semiconductor layer, and smoothing the surface of the substrate.

PALOALTO 47242 (2K) -4-